



Plastic-Encapsulate Transistors

DUAL TRANSISTOR (PNP+PNP)

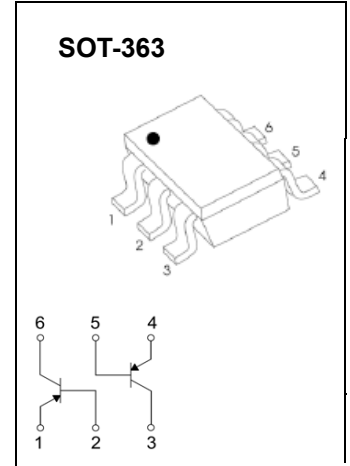
FEATURES

- Complementary to MMDT5551DW
- Small Surface Mount Package
- Ideal for Medium Power Amplification and Switching

MARKING: 2L

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

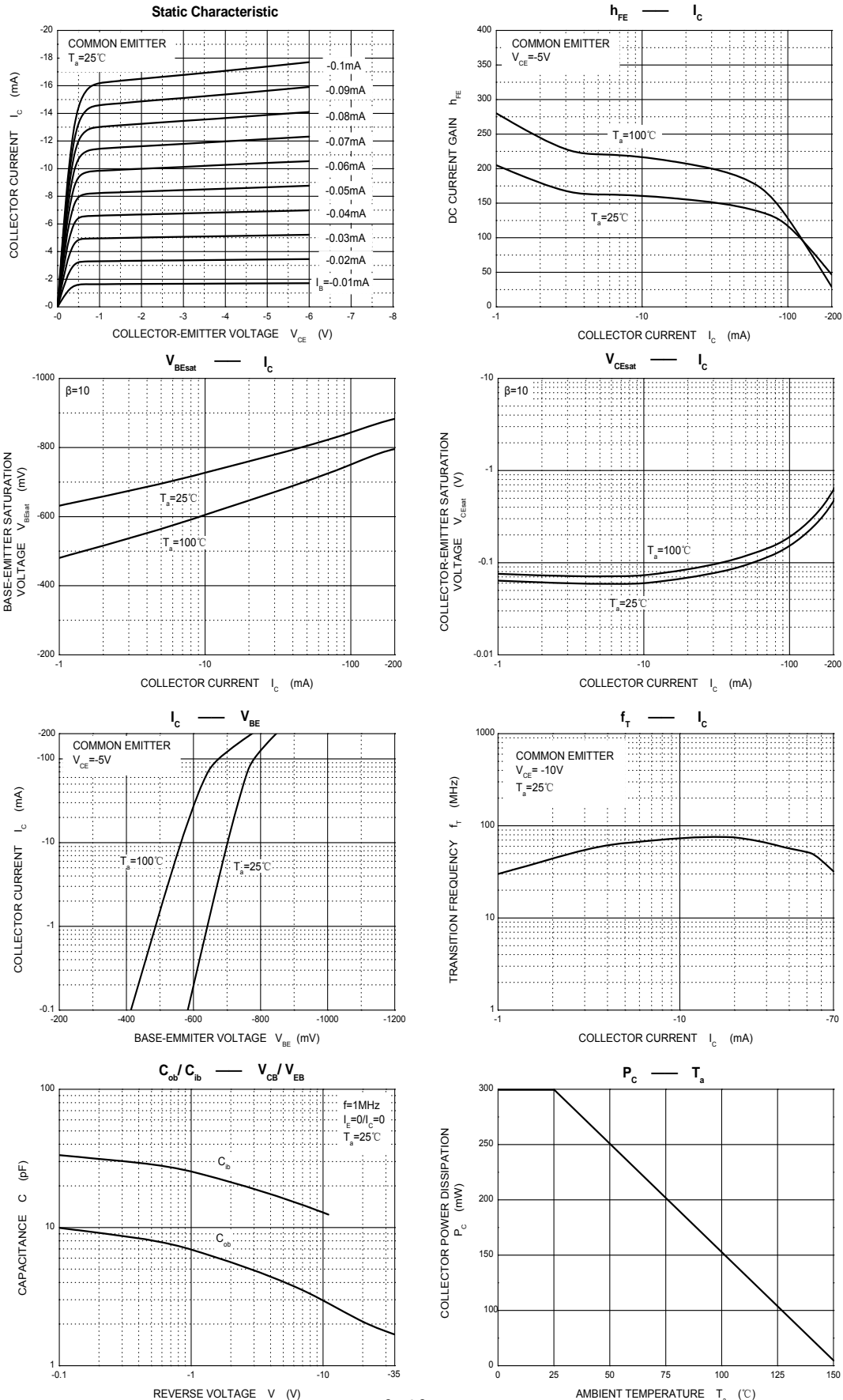
Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-160	V
V _{CEO}	Collector-Emitter Voltage	-150	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current	-600	mA
P _C	Collector Power Dissipation	300	mW
R _{θJA}	Thermal Resistance From Junction To Ambient	625	°C/W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

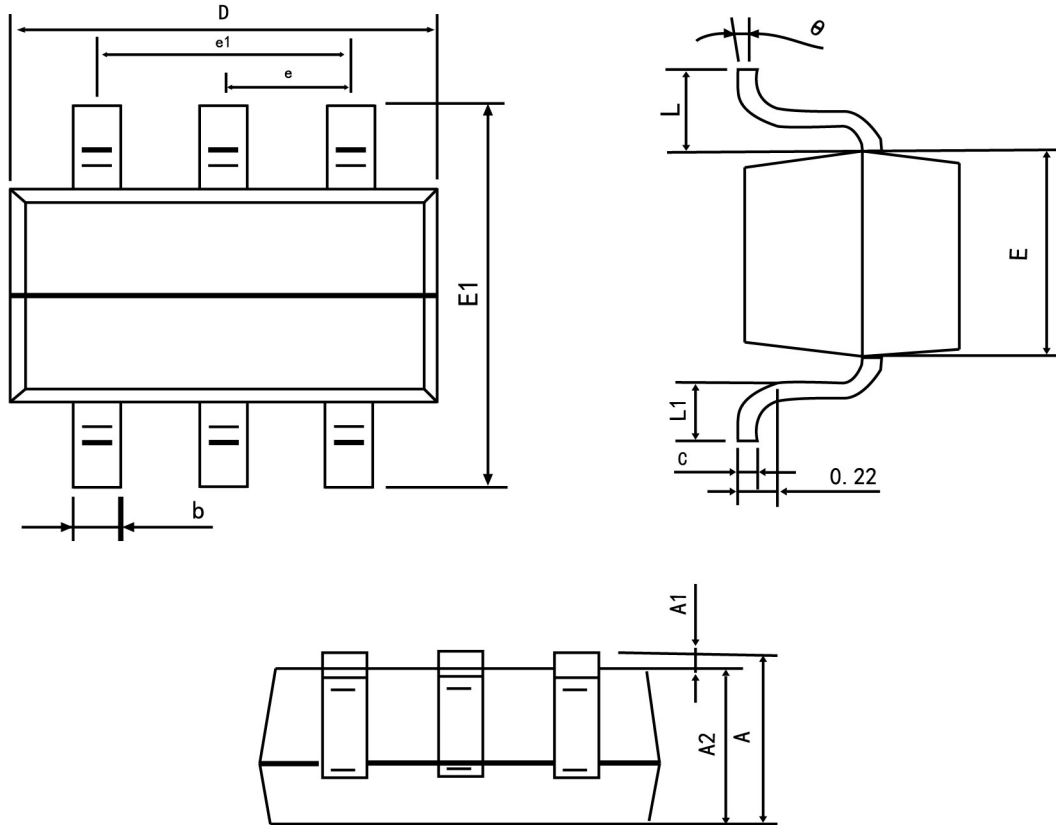
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-160			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-150			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-10μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-120V, I _E =0			-50	nA
Emitter cut-off current	I _{EBO}	V _{EB} =-3V, I _C =0			-50	nA
DC current gain	h _{FE}	V _{CE} =-5V, I _C =-1mA	50			
		V _{CE} =-5V, I _C =-10mA	60		300	
		V _{CE} =-5V, I _C =-50mA	50			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-50mA, I _B =-5mA			-0.5	V
		I _C =-10mA, I _B =-1mA			-0.2	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-50mA, I _B =-5mA			-1	V
		I _C =-10mA, I _B =-1mA			-1	V
Transition frequency	f _T	V _{CE} =-10V, I _C =-10mA, f=100MHz	100			MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz			6	pF

Typical Characteristics





SOT-363-Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.900	1.100
A1	0.000	0.100
A2	0.900	1.000
b	0.150	0.350
c	0.080	0.150
D	2.000	2.200
E	1.150	1.350
E1	2.150	2.450
e	0.650 TYP	
e1	1.200	1.400
L	0.525 REF	
L1	0.260	0.460
θ	0°	8°